## Code No: 131AK

## R16

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD
B.Tech I Year I Semester Examinations, May/June - 2017

BASIC ELECTRICAL AND ELECTRONICS ENGINEERING (Common to EEE, ECE, CSE, EIE, IT)
Time: 3 hours
Max. Marks: 75
Note: This question paper contains two parts A and B.
Part A is compulsory which carries 25 marks. Answer all questions in Part A. Part B consists of 5 Units. Answer any one full question from each unit. Each question carries 10 marks and may have $\mathrm{a}, \mathrm{b}, \mathrm{c}$ as sub questions.

## PART- A

(25 Marks)
1.a) State ohm's law and mention the limitations of it.
b) Mention the advantages of sinusoidal alternating quantity.
c) Explain what is meant by Bandwidth and Q factor?
d) Give the statement of Reciprocity theorem.
e) What is forward bias and reverse bias in a PN junction?
f) Define ripple factor. What is the value of ripple factor for FWR and HWR?
g) Why transistor is called as a current controlled device?
h) Explain how $h_{i e}$ is different from $\mathrm{h}_{\mathrm{fe}}$ in CE configuration.
i) How is drain current controlled in a JFET?
j) List some applications of varactor diode.

## PART-B

(50 Marks)
2.a) For the circuit shown in figure 1 , find the current flowing in all the branches.


Figure: 1
b) Find the rms value, average value and form factor of a half wave rectified voltage.[5+5]

OR
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3.a) Define the following:
i) Alternating Quantity
ii) R.M.S. Value
iii) Average value
iv) Form factor.
b) Deduce an expression for the equivalent capacitance of three capacitors connected in
i) Parallel
ii) Series.

Hence calculate the equivalent capacitance if three capacitors of capacitances 2, 4, and 8 micro - Farads are connected in 1) Series 2) Parallel
If a voltage of 10 V is connected, calculate the charge stored in each case.
4.a) A series circuit comprising R, L and C is supplied at $220 \mathrm{~V}, 50 \mathrm{~Hz}$. At resonance, the voltage across the capacitor is 550 V . The current at resonance is 1 A . Determine the circuit parameters $\mathrm{R}, \mathrm{L}$ and C .
b) In the network shown in figure 2, find the value of $\mathrm{Z}_{\mathrm{L}}$ so that the power transferred from the source is maximum. Also find $\mathrm{P}_{\text {max }}$.
[5+5]


Figure: 2
OR
5.a) A coil having a resistance of 10 ohms and an inductance of 0.2 H is connected in series with a $100 \times 10^{-6} \mathrm{~F}$ capacitor across a $230 \mathrm{~V}, 50 \mathrm{~Hz}$ supply, Calculate:
i) The active and reactive components of the current
ii) The voltage across the coil, Draw the phasor diagram.
b) Using Thevenin's theorem, calculate the current I through the resistance connected between the terminal A and B (All resistances are in ohms) as shown in figure 3. [5+5]

6.a) Draw and explain the V-I characteristics of a pn junction.
b) Compare Half wave rectifier, Full wave rectifier and Bridge rectifier in any four aspects.

## OR

7.a) What are the applications of the semiconductor diode? Explain each one with suitable circuit diagram.
b) A silicon diode operates at forward voltage of 0.4 V . Calculate the factor by which the current will be multiplied when the temperature is increased from $25^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$. [5+5]
8.a) Draw the input and output characteristics of n-p-n transistor in common base configuration and explain how they are obtained.
b) In a fixed bias circuit using n-p-n transistor, find the operating point if $\mathrm{V}_{\mathrm{CC}}=24 \mathrm{~V}$, $\mathrm{R}_{\mathrm{B}}=220 \mathrm{k}, \mathrm{R}_{\mathrm{C}}=4.7 \mathrm{k}$.

## OR

9.a) Draw the circuit and explain the characteristics of CB configuration.
b) Write short notes on thermal runaway problems.
10.a) What is a zener diode? Draw the equivalent circuit of an ideal zener in the break down region.
b) How is zener diode used as a voltage regulator?
11.a) Draw the circuit and explain the drain and gate characteristics of a JFET.
b) Give the parameter values and specifications of a JFET.

